

Amendments to the Specification:

Please make the following amendments to the specification (material to be inserted in replacement paragraphs or sections is in **bold and underline**, and material to be deleted is in ~~strikeout~~ or (if the deletion is of five or fewer consecutive characters or would be difficult to see) in double brackets [[]]).

Please replace the paragraph beginning at page 5, line 16, with the following rewritten paragraph:

It will be appreciated that in the examples discussed herein, the conductive properties of channel 80 (Figs. 2-5) will vary depending upon the voltage applied at gate electrode 60. At a certain gate voltage level, referred to as the turn-on or threshold voltage, the ability of the channel to transport charge in response to an applied potential is activated. At gate voltages below the threshold, the source-drain current in response to a ~~give~~ **given** source-drain potential typically does not change as the gate voltage is increased (or at least the drain current does not significantly increase; see the related discussion of Fig. 7 below). Once the threshold voltage is achieved, however, increases in gate voltage produce a steadily increasing source-drain current.

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AMENDMENT
Serial No. 10/763,354
HP Docket No. 200311820-1
KH Docket No. HPC 3E8

Please replace the paragraph beginning at page 5, line 26, with the following rewritten paragraph:

In certain applications, it will be desirable that the transistor threshold voltage ~~by~~ be consistently and reproducibly controlled over some desired range of voltage. Furthermore, it will at times be desirable that the transistor be configured with a threshold voltage of zero volts.